

# **Thyristor \ Diode Module**

= 2x 1600 V

110 A

 $V_{\mathsf{T}}$ 1.21 V

## Phase leg

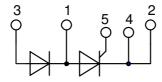
#### Part number

### **MCMA110PD1600TB**



Backside: isolated

**F1** E72873



## Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

## **Applications:**

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

## Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- · Reduced weight
- Advanced power cycling

#### Terms \_Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you.

Should you intend to use the product in aviation, in health or live endangering or life support applications, please notify. For any such application we urgently recommend

- to perform joint risk and quality assessments; the conclusion of quality agreements;
- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

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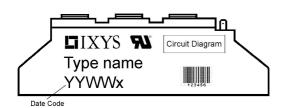
# MCMA110PD1600TB

Thyristo		Candisia		Ì	Ratings		
Symbol	Definition	Conditions	T 0500	min.	typ.	max.	Un
V <sub>RSM/DSM</sub>	max. non-repetitive reverse/forwa		$T_{VJ} = 25^{\circ}C$			1700	ì
V <sub>RRM/DRM</sub>	max. repetitive reverse/forward bl		$T_{VJ} = 25^{\circ}C$			1600	<u> </u>
I <sub>R/D</sub>	reverse current, drain current	$V_{R/D} = 1600 \text{ V}$	$T_{VJ} = 25^{\circ}C$			100	μ
		$V_{R/D} = 1600 \text{ V}$	$T_{VJ} = 140$ °C			10	m
V <sub>T</sub>	forward voltage drop	$I_T = 110 A$	$T_{VJ} = 25^{\circ}C$			1.24	¦ '
		$I_{T} = 220 \text{ A}$				1.52	'
		$I_T = 110 A$	$T_{VJ} = 125$ °C			1.21	! !
		$I_{T} = 220 \text{ A}$				1.57	! ! !
I <sub>TAV</sub>	average forward current	$T_{c} = 85^{\circ}C$	$T_{VJ} = 140$ °C			110	i ! !
I <sub>T(RMS)</sub>	RMS forward current	180° sine				170	! !
V <sub>T0</sub>	threshold voltage		T <sub>vJ</sub> = 140°C			0.85	,
r <sub>T</sub>	slope resistance } for power lo	oss calculation only				3.3	m
R <sub>thJC</sub>	thermal resistance junction to cas	e				0.3	K/V
R <sub>thCH</sub>	thermal resistance case to heatsi	nk			0.20		K/V
P <sub>tot</sub>	total power dissipation		T <sub>C</sub> = 25°C			380	٧
I <sub>TSM</sub>	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			1.90	k,
10m	-	t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			2.05	k,
		t = 10 ms; (50 Hz), sine	T <sub>v.i</sub> = 140°C			1.62	1
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			1.75	k
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			18.1	
	- Land Co. Looning	t = 8,3  ms; (60  Hz),  sine	$V_R = 0 V$			17.5	i i
		t = 0.5  ms; (50 Hz), sine	T <sub>v.i</sub> = 140°C				kA <sup>2</sup>
		t = 8,3  ms; (60  Hz),  sine	$V_R = 0 V$			12.7	į
C,	junction capacitance	$V_{\rm R} = 400  \text{V}  \text{f} = 1  \text{MHz}$	$T_{VJ} = 25^{\circ}C$		95	12.7	pl
			$T_{\rm VJ} = 23  \rm C$ $T_{\rm C} = 140  \rm ^{\circ} \rm C$		95	10	V
P <sub>GM</sub>	max. gate power dissipation	$t_P = 30 \mu s$	1 <sub>C</sub> = 140 C				į.
_		$t_{P} = 300 \mu s$				5	۷
P <sub>GAV</sub>	average gate power dissipation					0.5	۷
(di/dt) <sub>cr</sub>	critical rate of rise of current	$T_{VJ} = 140 ^{\circ}\text{C}; f = 50 \text{Hz}$	•			150	A/μ
		$t_p = 200 \mu s; di_g/dt = 0.45 A/\mu s; -$					
			on-repet., $I_T = 110 A$				A/μ
(dv/dt) <sub>cr</sub>	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140$ °C			1000	V/μ
		R <sub>GK</sub> = ∞; method 1 (linear volta					 
$V_{GT}$	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$			1.5	١
			$T_{VJ} = -40$ °C			1.6	١
I <sub>GT</sub>	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25$ °C			150	m
			$T_{VJ} = -40$ °C			200	m
V <sub>GD</sub>	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}C$			0.2	١
I <sub>GD</sub>	gate non-trigger current					10	m
I <sub>L</sub>	latching current	t <sub>p</sub> = 10 μs	$T_{VJ} = 25$ °C			200	m
_		$I_{\rm G} = 0.45  \text{A};  \text{di}_{\rm G}/\text{dt} = 0.45  \text{A}/\mu \text{s}$					: ! ! !
I <sub>H</sub>	holding current	$V_D = 6 \text{ V } R_{GK} = \infty$	T <sub>vJ</sub> = 25°C			200	m
	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25$ °C			2	μ
t <sub>gd</sub>	Jane 11 mod dolay amo					_	μ
•ga		$I_{a} = () 45 \Delta \cdot di_{-}/dt - 0.45 \Delta/03$					
t <sub>q</sub>	turn-off time	$I_G = 0.45 \text{ A}; \text{ di}_G/\text{dt} = 0.45 \text{ A}/\mu\text{s}$			185		μ



## **MCMA110PD1600TB**

Package	Package TO-240AA			Ratings				
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I <sub>RMS</sub>	RMS current	per terminal					200	Α
T <sub>VJ</sub>	virtual junction temperature				-40		140	°C
T <sub>op</sub>	operation temperature				-40		125	°C
T <sub>stg</sub>	storage temperature				-40		125	°C
Weight						81		g
M <sub>D</sub>	mounting torque				2.5		4	Nm
$\mathbf{M}_{_{T}}$	terminal torque				2.5		4	Nm
d <sub>Spp/App</sub>	araanaga diatanaa an aurfa	oo Latriking diatanga through air	terminal to terminal	13.0	9.7			mm
d <sub>Spb/Apb</sub>	creepage distance on surface   striking distance thro		terminal to backside	16.0	16.0			mm
V	isolation voltage	t = 1 second	50/60 Hz. BMS: IIsoi ≤ 1 mA		4800			٧
		t = 1 minute			4000			٧



## Part description

M = Module

M = Module
C = Thyristor (SCR)
M = Thyristor
A = (up to 1800V)
110 = Current Rating [A]
PD = Phase leg

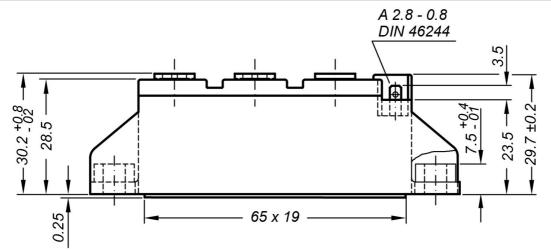
1600 = Reverse Voltage [V] TB = TO-240AA-1B

Ordering	Ordering Number	Ordering Number Marking on Product		Quantity	Code No.	
Standard	MCMA110PD1600TB	MCMA110PD1600TB	Box	6	515919	

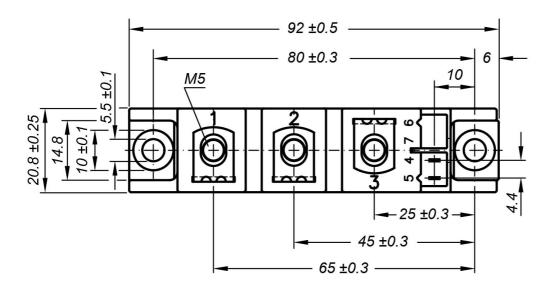
<b>Equivalent Circuits for Simulation</b>			* on die level	$T_{VJ} = 140 ^{\circ}\text{C}$
$I \rightarrow V_0$	— R <sub>o</sub>	Thyristor		
V <sub>0 max</sub>	threshold voltage	0.85		V
$R_{0 \; \text{max}}$	slope resistance *	2.1		$m\Omega$



## Outlines TO-240AA

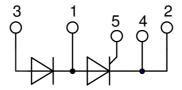


General tolerance: DIN ISO 2768 class "c"



Optional accessories: Keyed gate/cathode twin plugs Wire length: 350 mm, gate = white, cathode = red UL 758, style 3751

Type **ZY 200L** (L = Left for pin pair 4/5)





## **Thyristor**

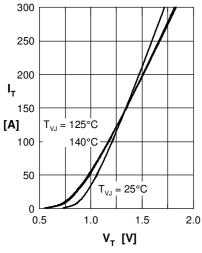


Fig. 1 Forward characteristics

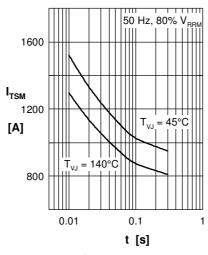


Fig. 2 Surge overload current  $I_{TSM}$ : crest value, t: duration

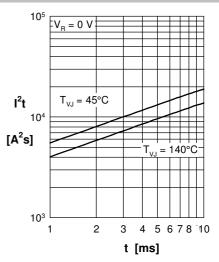


Fig. 3 I<sup>2</sup>t versus time (1-10 s)

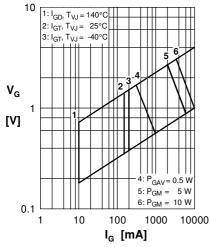


Fig. 4 Gate voltage & gate current

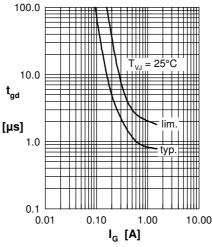


Fig. 5 Gate controlled delay time t<sub>ad</sub>

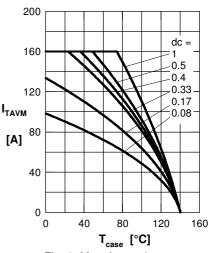


Fig. 6 Max. forward current at case temperature

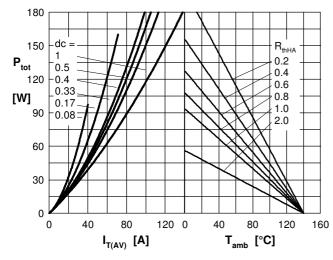


Fig. 7a Power dissipation versus direct output current Fig. 7b and ambient temperature

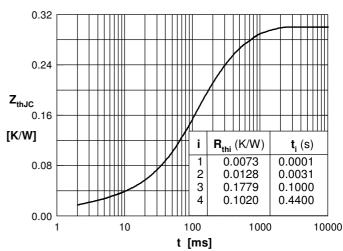


Fig. 8 Transient thermal impedance junction to case